

2024 ADVANCED MATERIALS CHARACTERIZATION *workshop*

Tuesday & Wednesday, June 4 & 5, 2024



Atom Probe Tomography

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Sr. Research Scientist

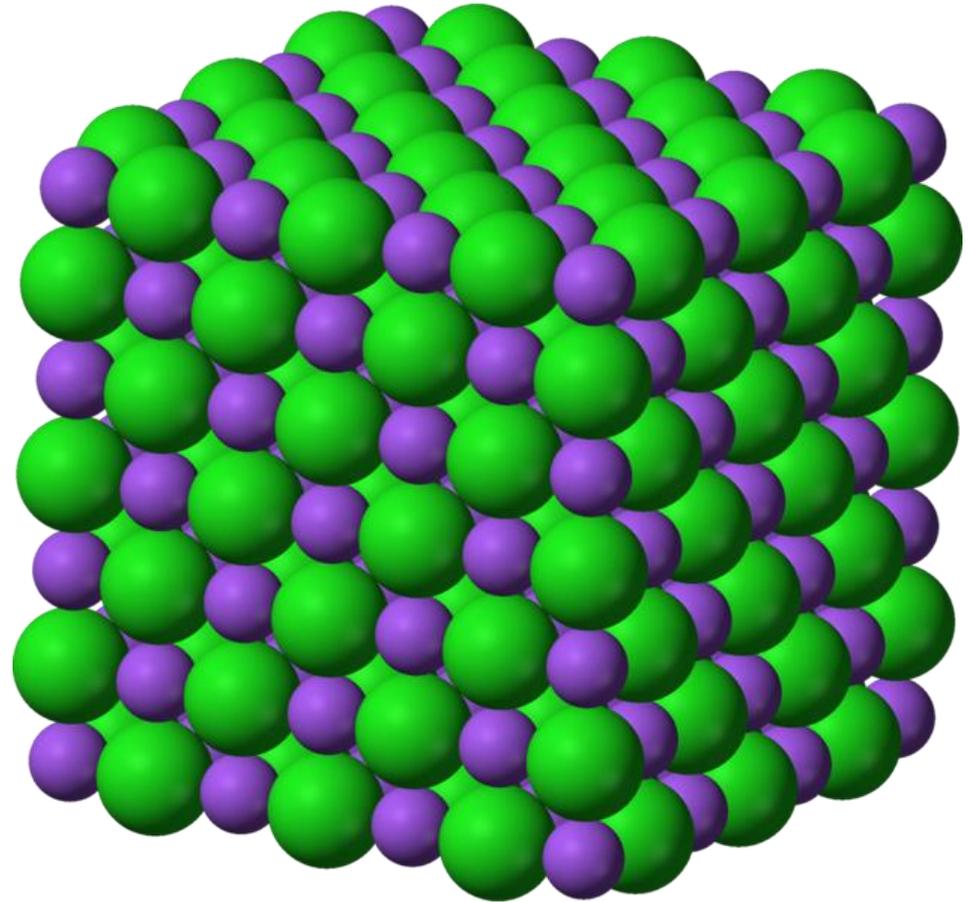
Materials Research Laboratory
MRL.Illinois.edu
University of Illinois at Urbana-Champaign

Atomistic Structure of Matter

Atom: derived from the ancient Greek word *atomos*, which means “uncuttable” (4th Century BC).

Modern view of the structure of an atom was derived by Rutherford (1913) and Bohr (1913).

Experiments on atomic nature of materials (packing of atoms in crystals) was deduced by Bragg and Bragg (1913).



Adapted from D.J. Larson et al., Local Electrode APT, book 2013

<https://commons.wikimedia.org/wiki/File:Sodium-chloride-3D-ionic.png>



Atom Probe Tomography

Spatial Resolution

0.1 – 0.3 nm in depth
0.3 – 0.5 nm laterally

Field of View

100 – 200 nm laterally

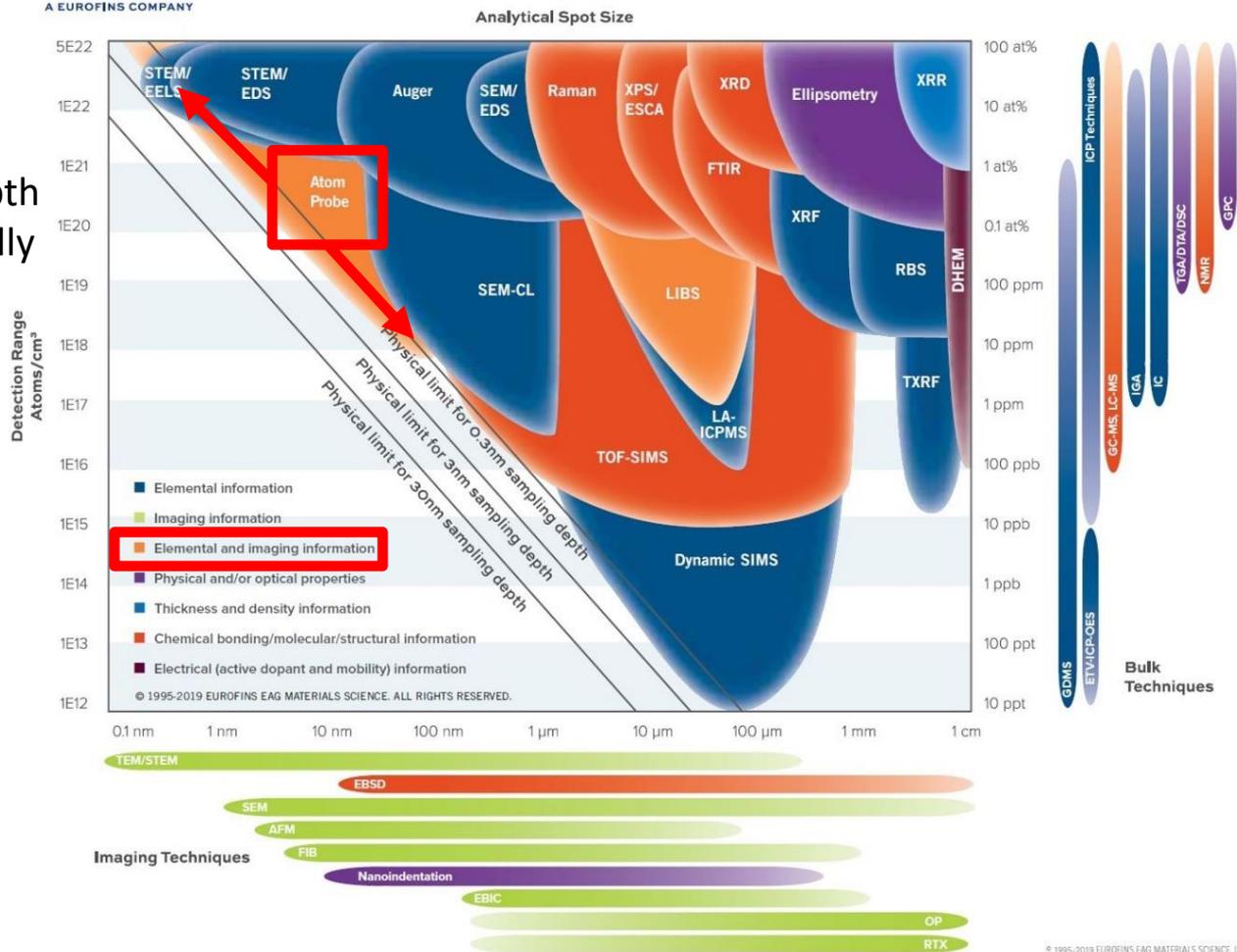
Time-of-Flight Mass Analysis

Mass range from 1 – 600 amu

Complementary to TEM

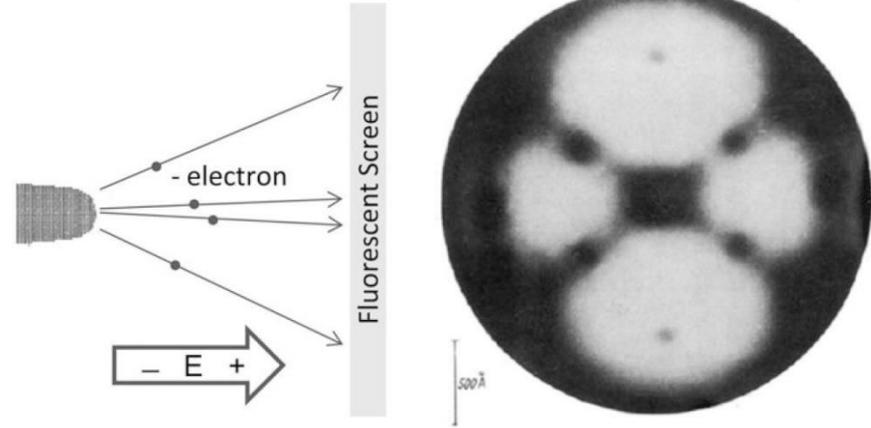
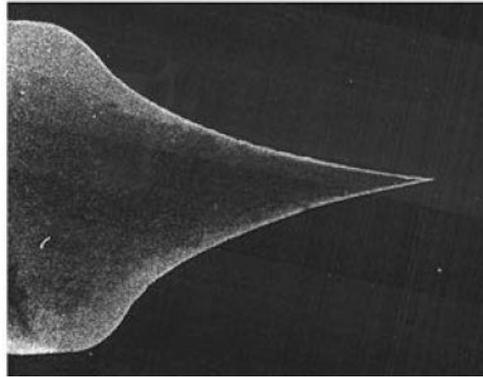


ANALYTICAL RESOLUTION VS. DETECTION LIMIT



Field Electron Emission Microscope (FEEM)

Erwin Wilhelm Müller - 1935



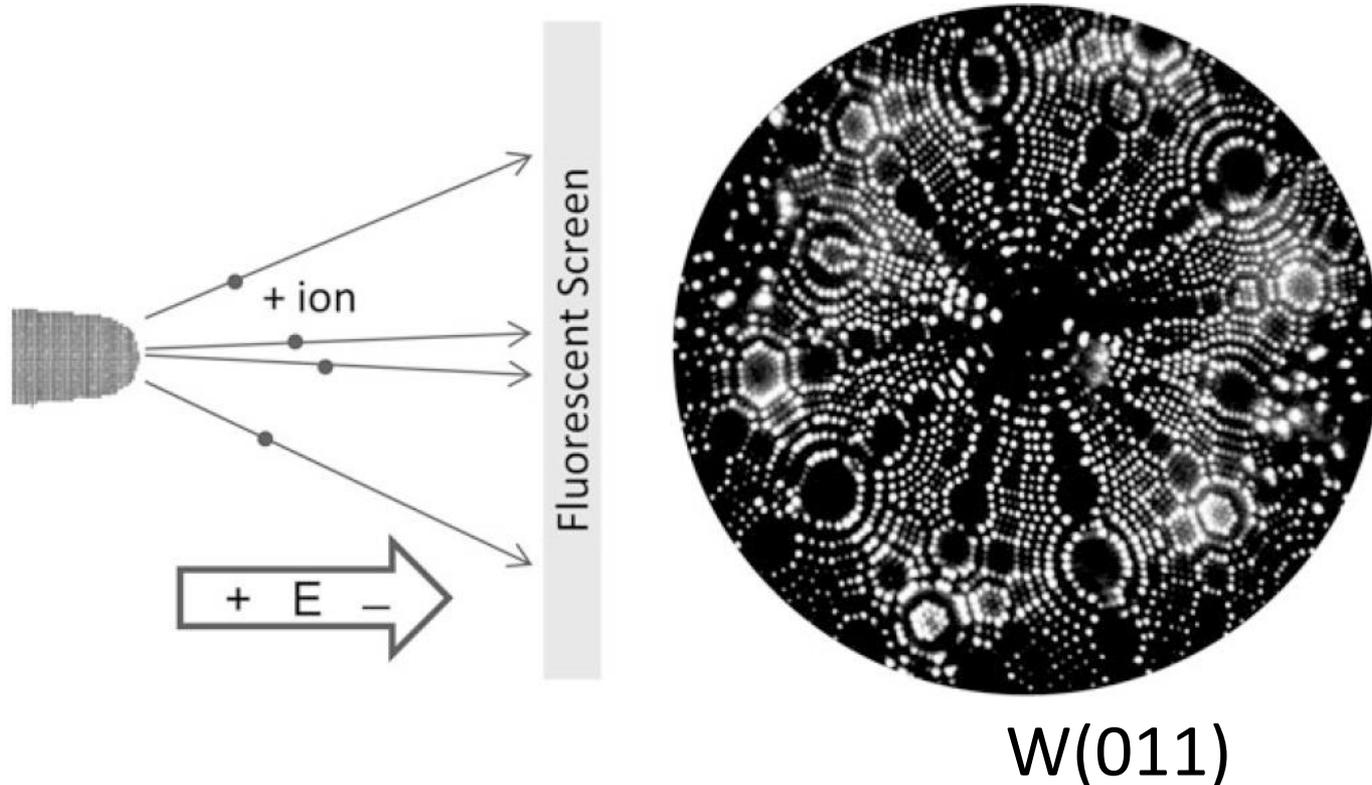
- 10^9 V/m needed to strip an electron from an atom
- Sharp point produces enhanced electric field
- 10,000 V with 1 μm tip radius $\Rightarrow 10^9$ V/m

Adapted from D.J. Larson et al., Local Electrode APT, book 2013

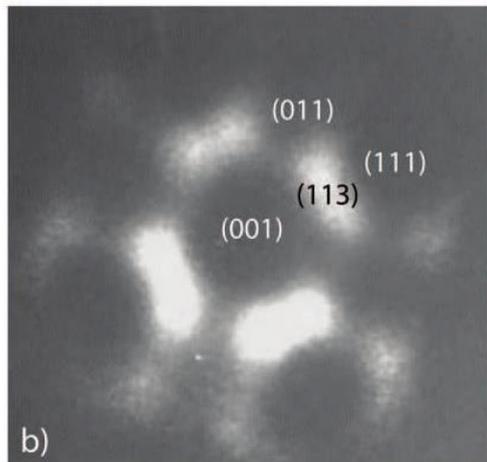
Field Ion Microscope (FIM)

Kanwar Bahadur and Erwin W. Müller - 1955

10^{-3} Pa He imaging gas, Tip cooled to 20-80K, Very sharp tip: 80 nm or less



Adapted from D.J. Larson et al., Local Electrode APT, book 2013

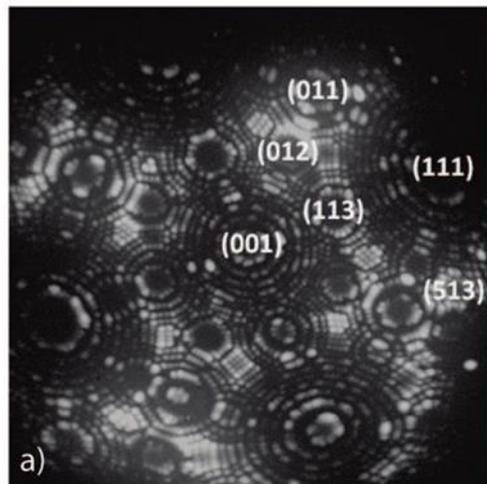
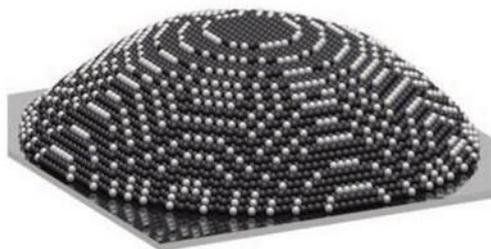
I

FEM (thermal form), Ni(001)

M. Moors et al., ACS-Nano 3 (2009) 511



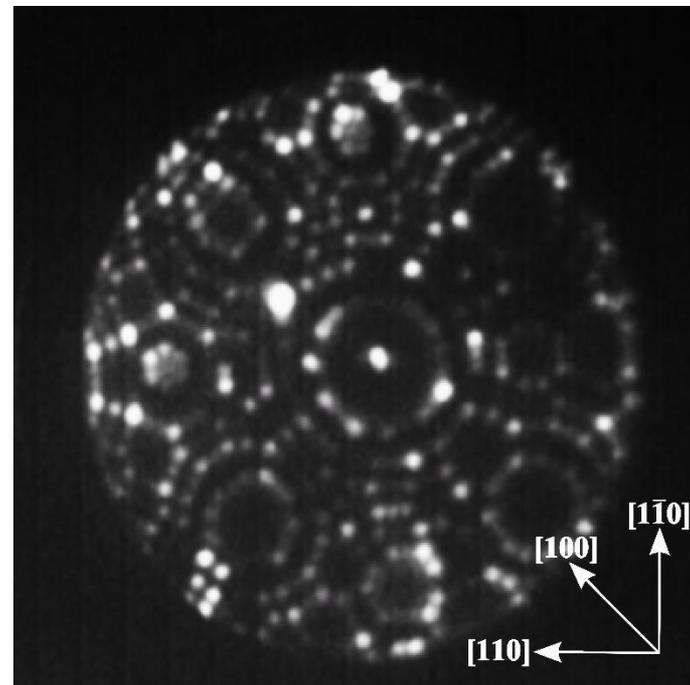
(Ni: cubic close packed)



FIM (field form), Ni(001)

M. Moors et al., ACS-Nano 3 (2009) 511

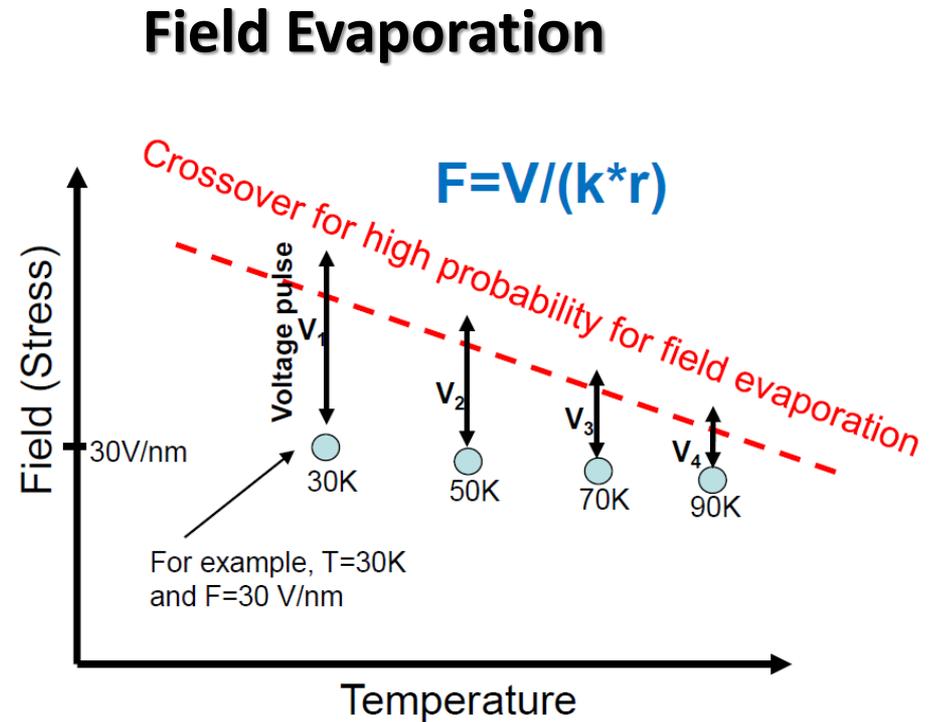
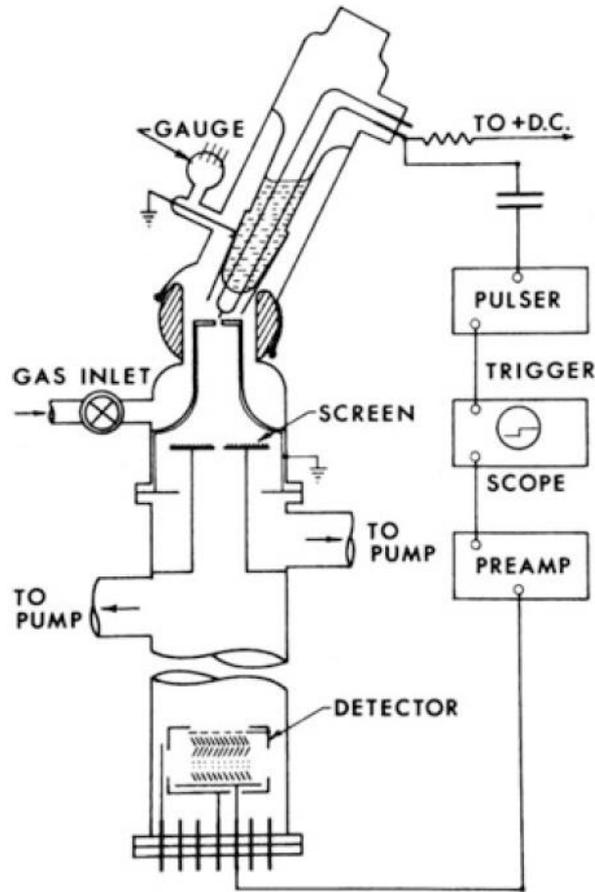
(W: BCC)



FIM (field form), W(001)

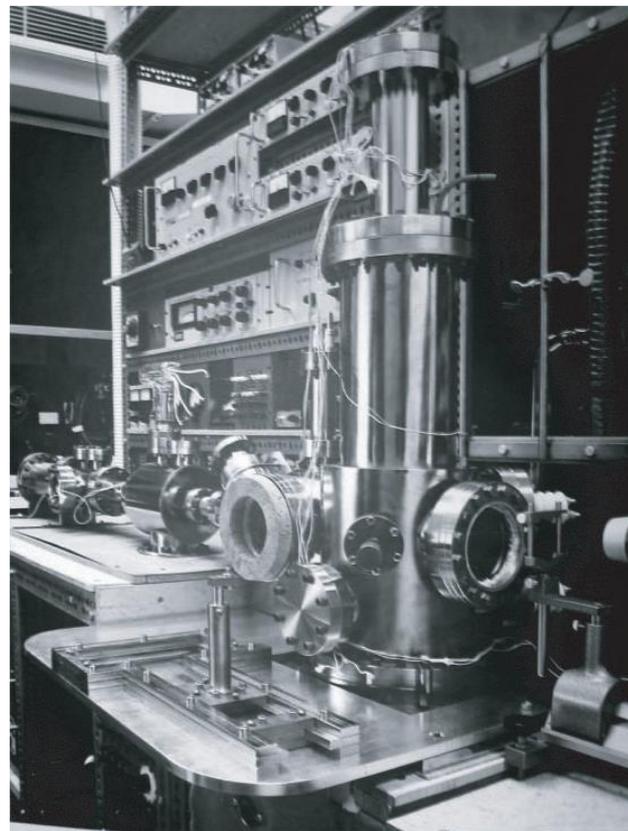
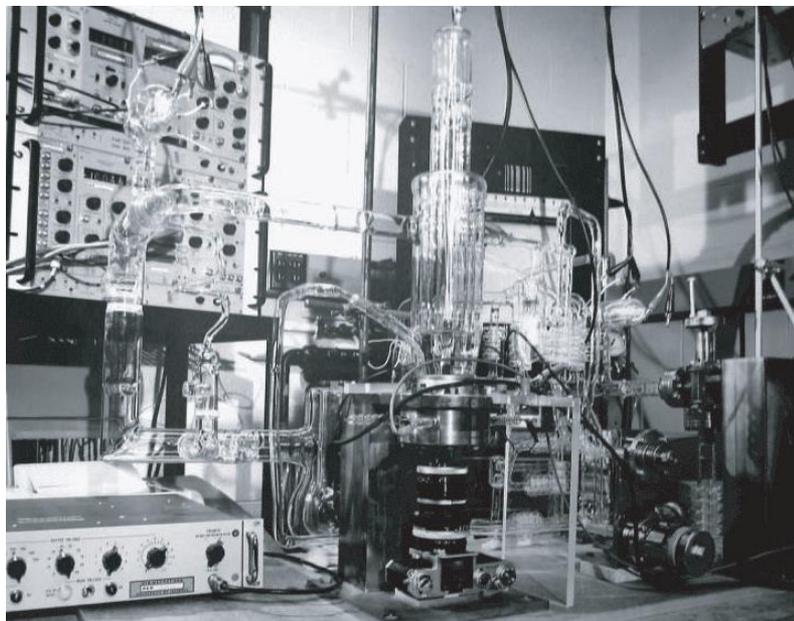
T. Olewicz et al., PRB 89 (2014) 235408

Atom Probe Field Ion Microscope – Voltage Mode

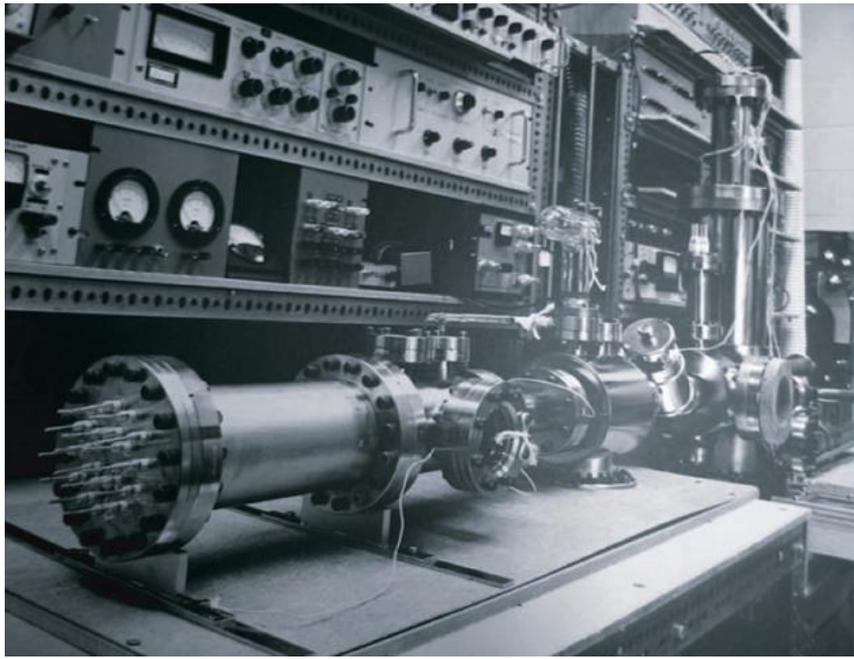


E. W. Müller, J. A. Panitz and S. B. McLane,
The atom-probe field ion microscope. Rev.
Sci. Instrum. **39** (1968) 83–86.

Adapted from: CAMECA, 2019



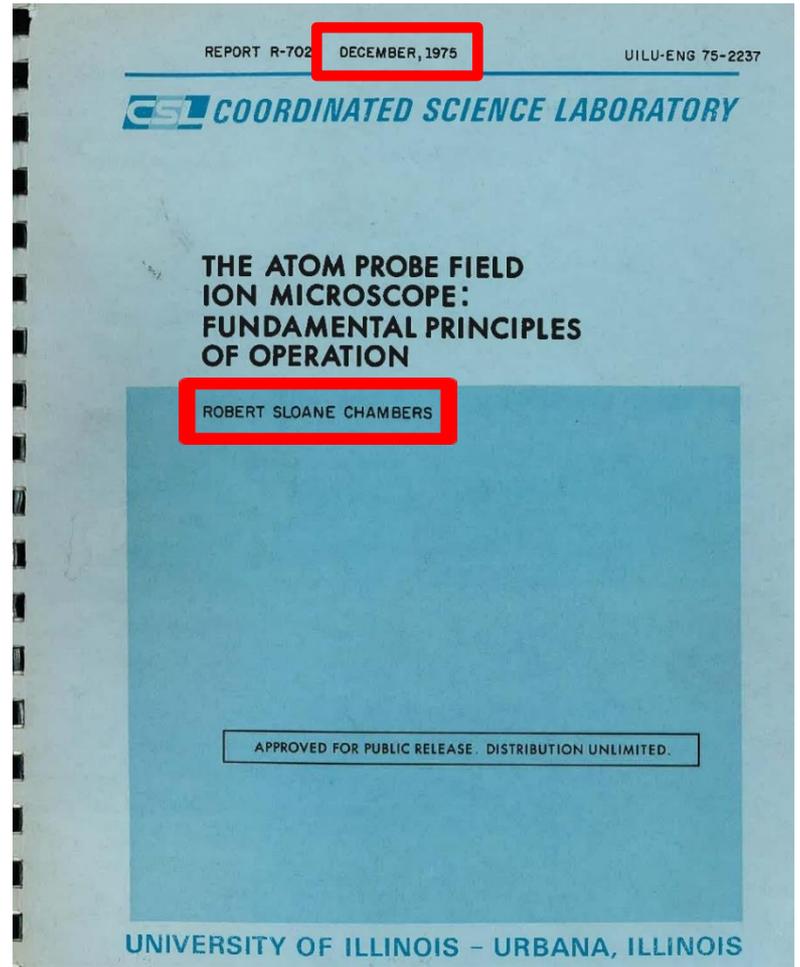
1968-1976: Prof. Gert Ehrlich and Rob Chambers;
FIM stand alone (glass) – left,
FIM side of FIM-AP (all metal) – right.



1968-1976: Prof. Gert Ehrlich and Rob Chambers;
AP side of FIM-AP (all metal).

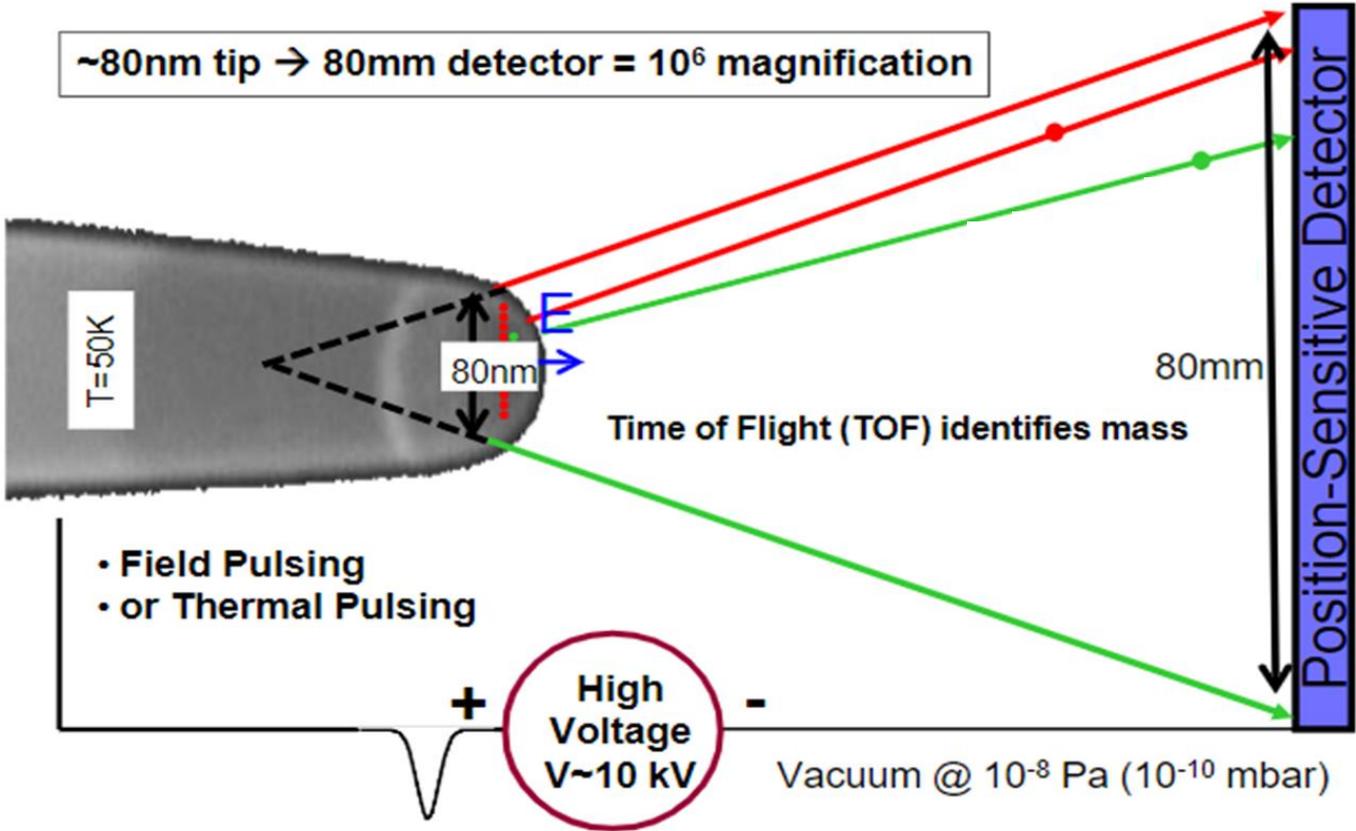


Gert Ehrlich
1926-2012



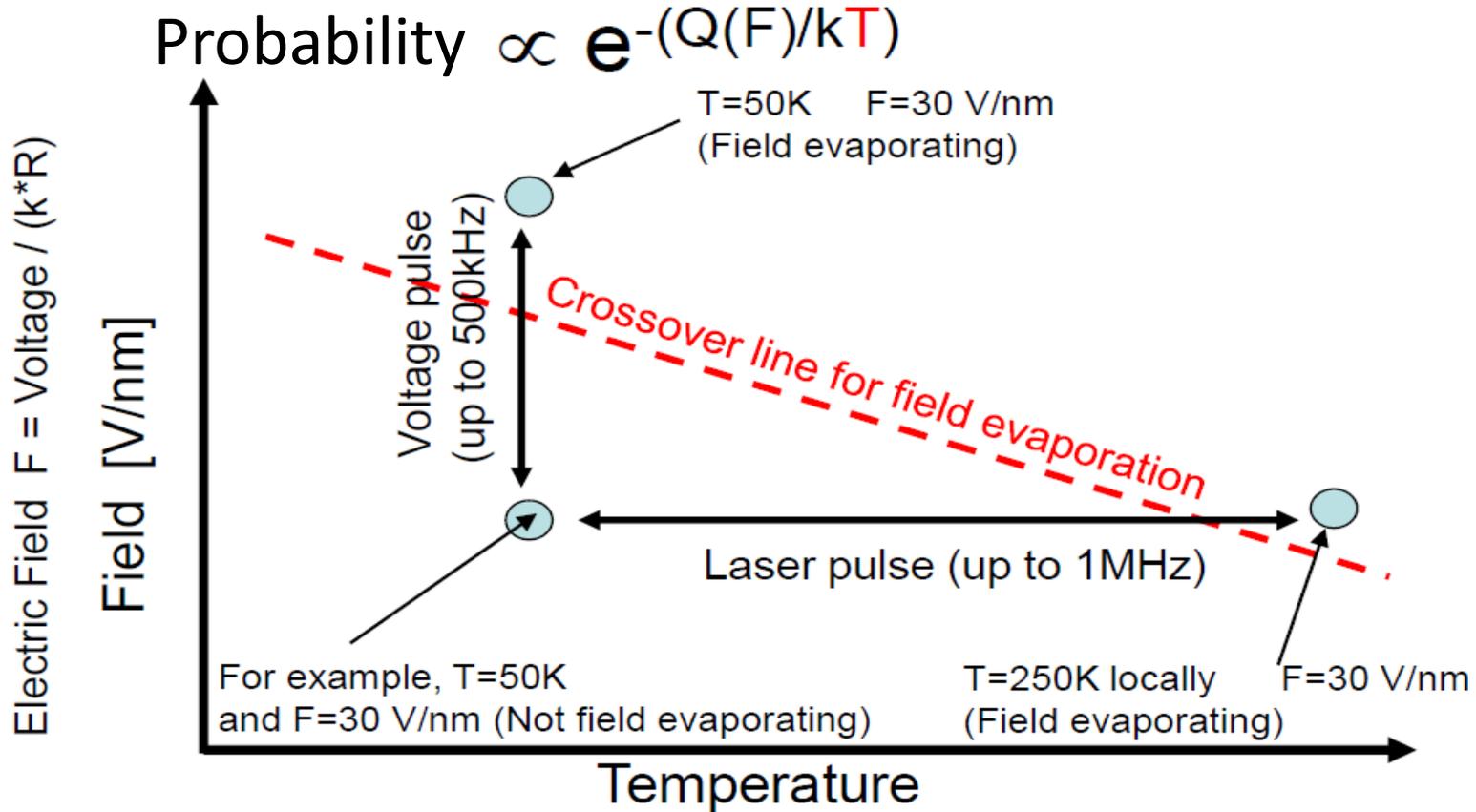
R.S. Chambers and G. Ehrlich, J. Vac. Sci. Technol., **13** (1), 273, 1976.

Atom Probe projection system



Adapted from: CAMECA, 2019

Atom Probe Ion Emission

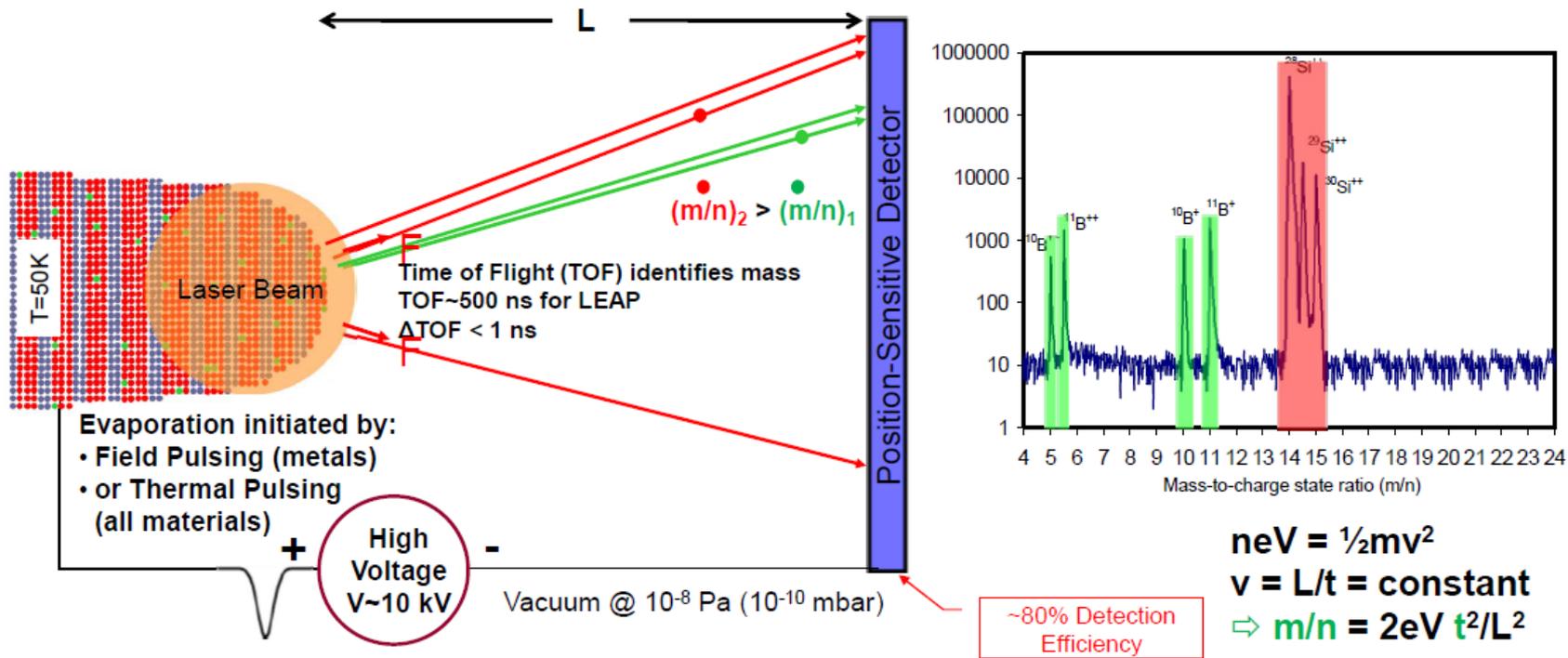


Adapted from: CAMECA, 2019

Field Evaporation of Ions – Mass Spectrometry

Description of Atom-Probe Operation

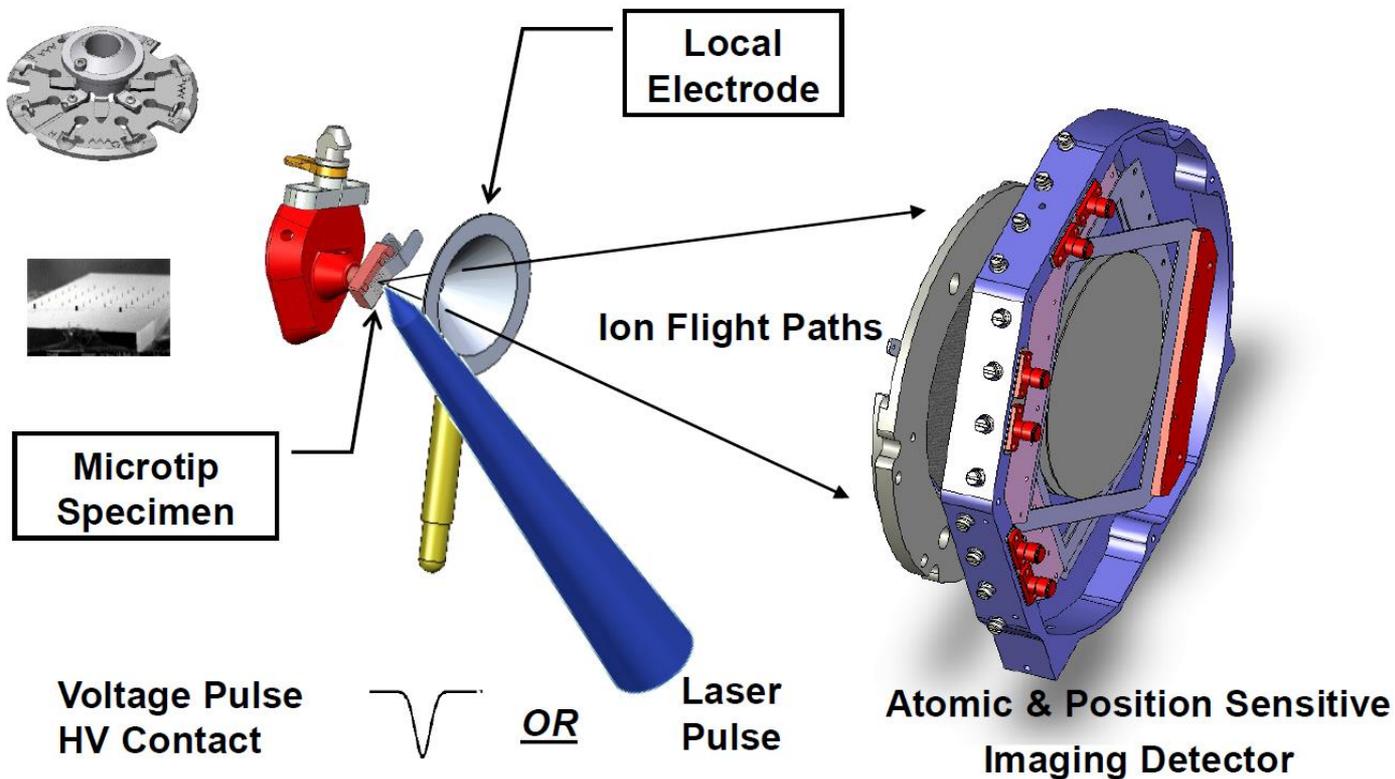
Atom Probe = projection imaging with time-of-flight mass spectrometer



Local Electrode Atom Probe

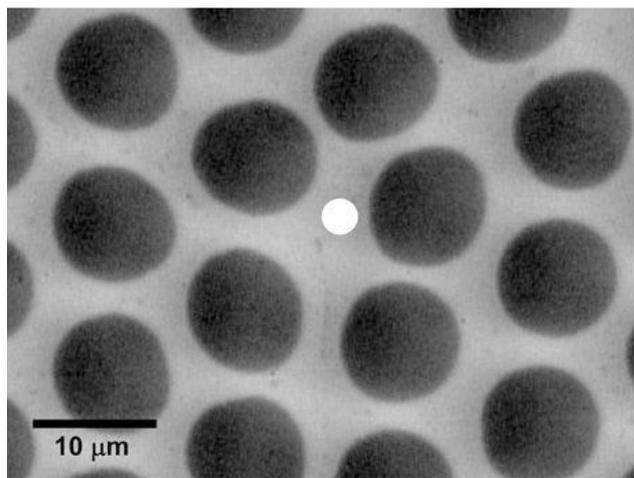


The LEAP[®] Microscope Geometry

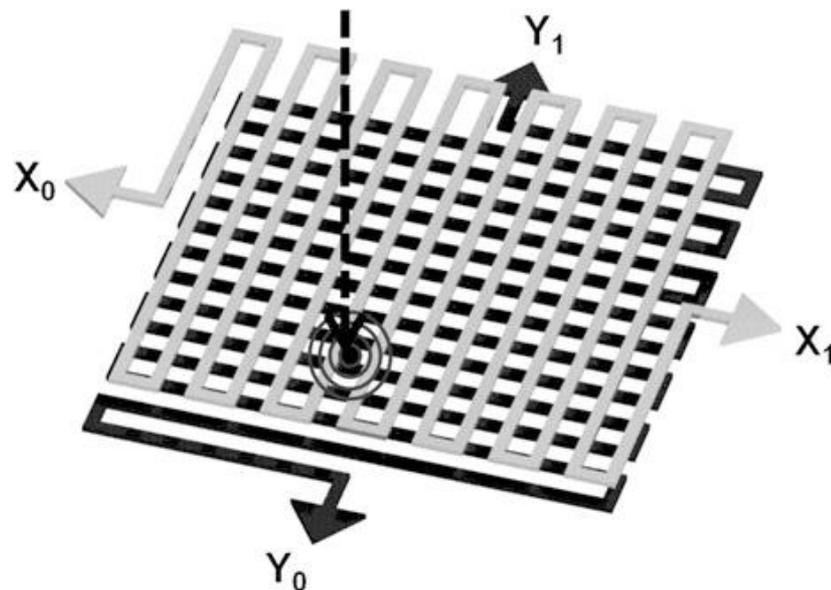


Straight Flight Path 'DT-200' Shown

Microchannel Plate (MCP)



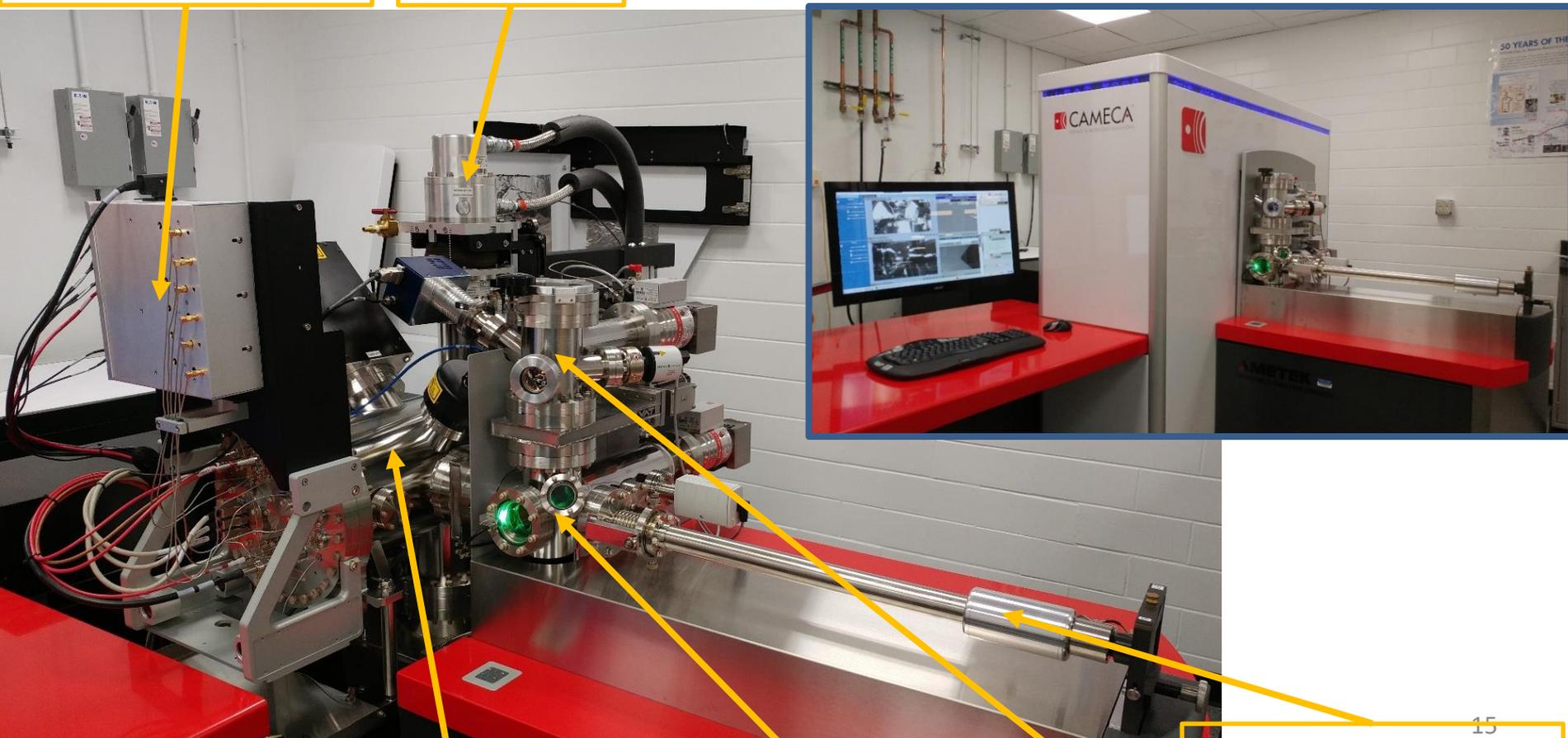
Delay Line Anode (DLA)



Adapted from D.J. Larson et al., Local Electrode APT, book 2013

Counting Electronics

Tip Cooling



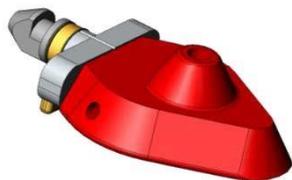
Analysis Chamber

Buffer Chamber

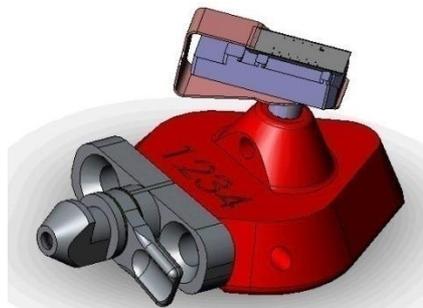
Load Lock

15
Magnetic (Lin-Rot)
Manipulator

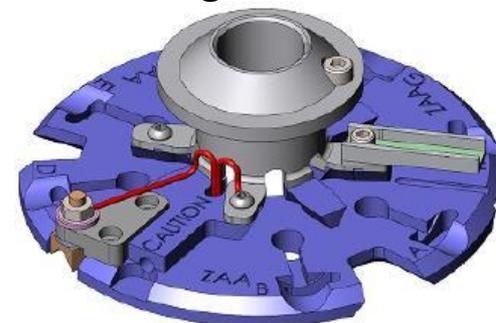
Sample Puck



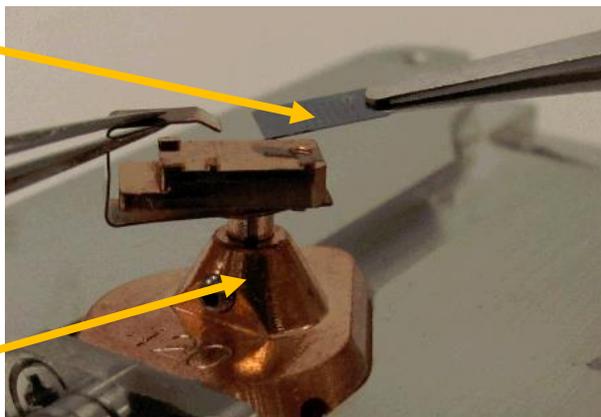
Puck with Sample Coupon



Sample or Local Electrode Storage Carousel

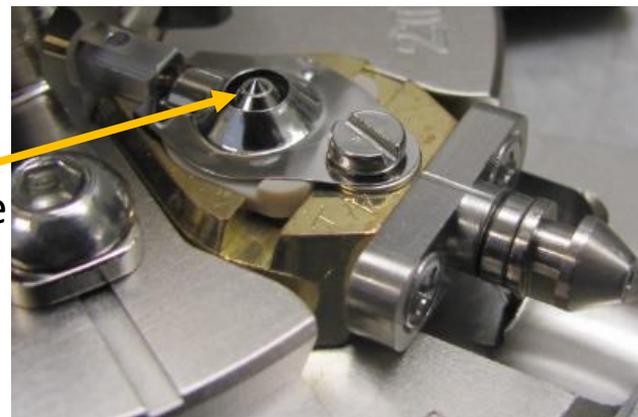


Coupon



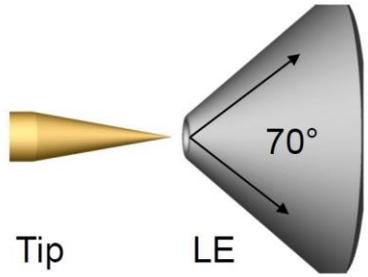
Sample Puck

Local Electrode



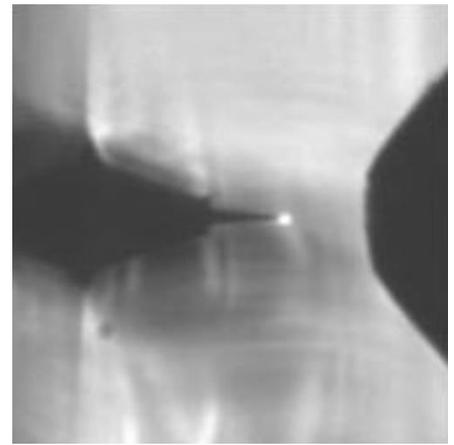
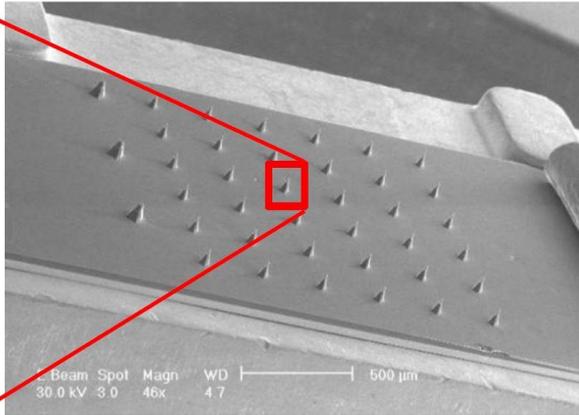
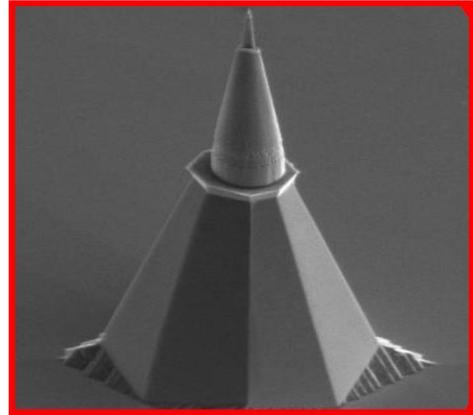
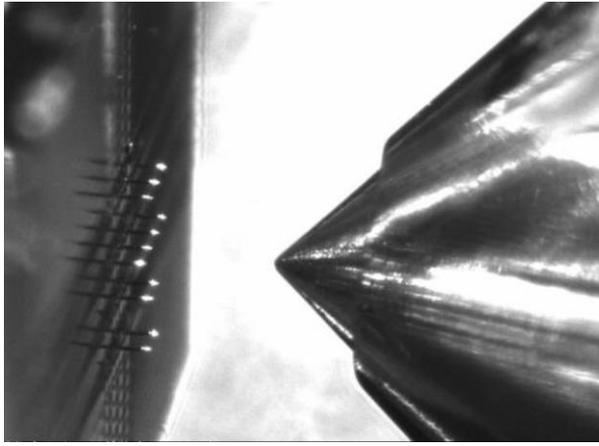
<https://www.atomprobe.com/keyaplinks/options-accessories-consumables>

Local Electrode Atom Probe

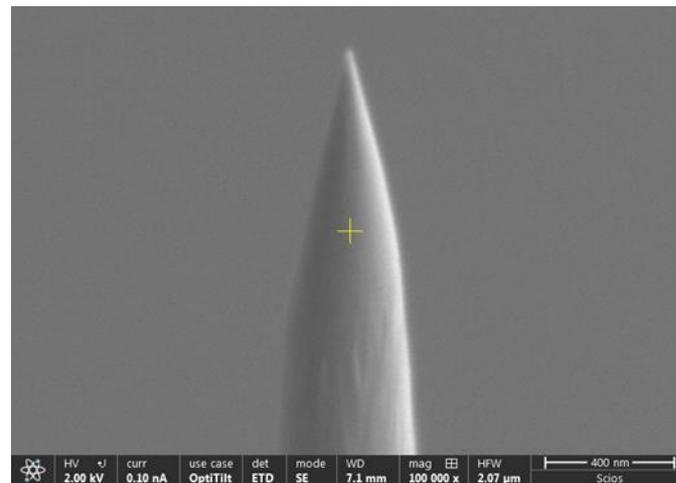


Model Parameters

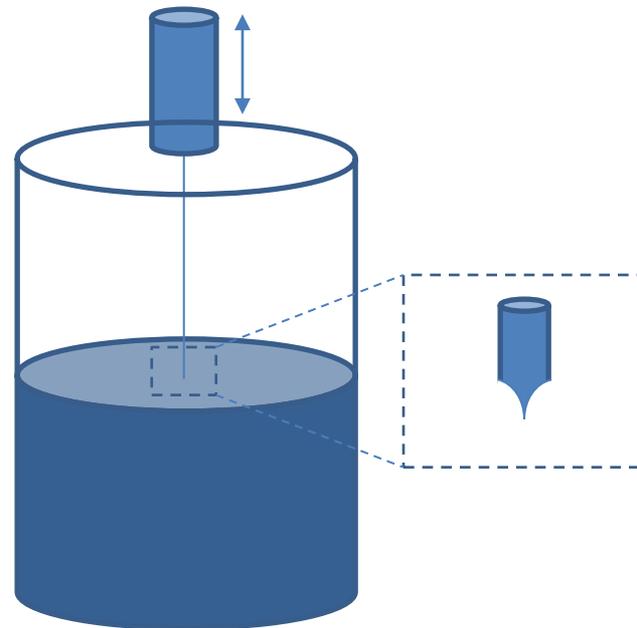
- ◆ 50 nm tip radius
- ◆ 10° shank angle
- ◆ 50 micron wire
- ◆ 1 mm long
- ◆ Specimen-to-local-electrode distance is that required to permit a 70° geometric FOV



- Requirements for APT samples
 - Specimens must be sharp with a radius of curvature of ~ 100 nm or less
 - Feature of interest within 50 to 150 nm of specimen apex

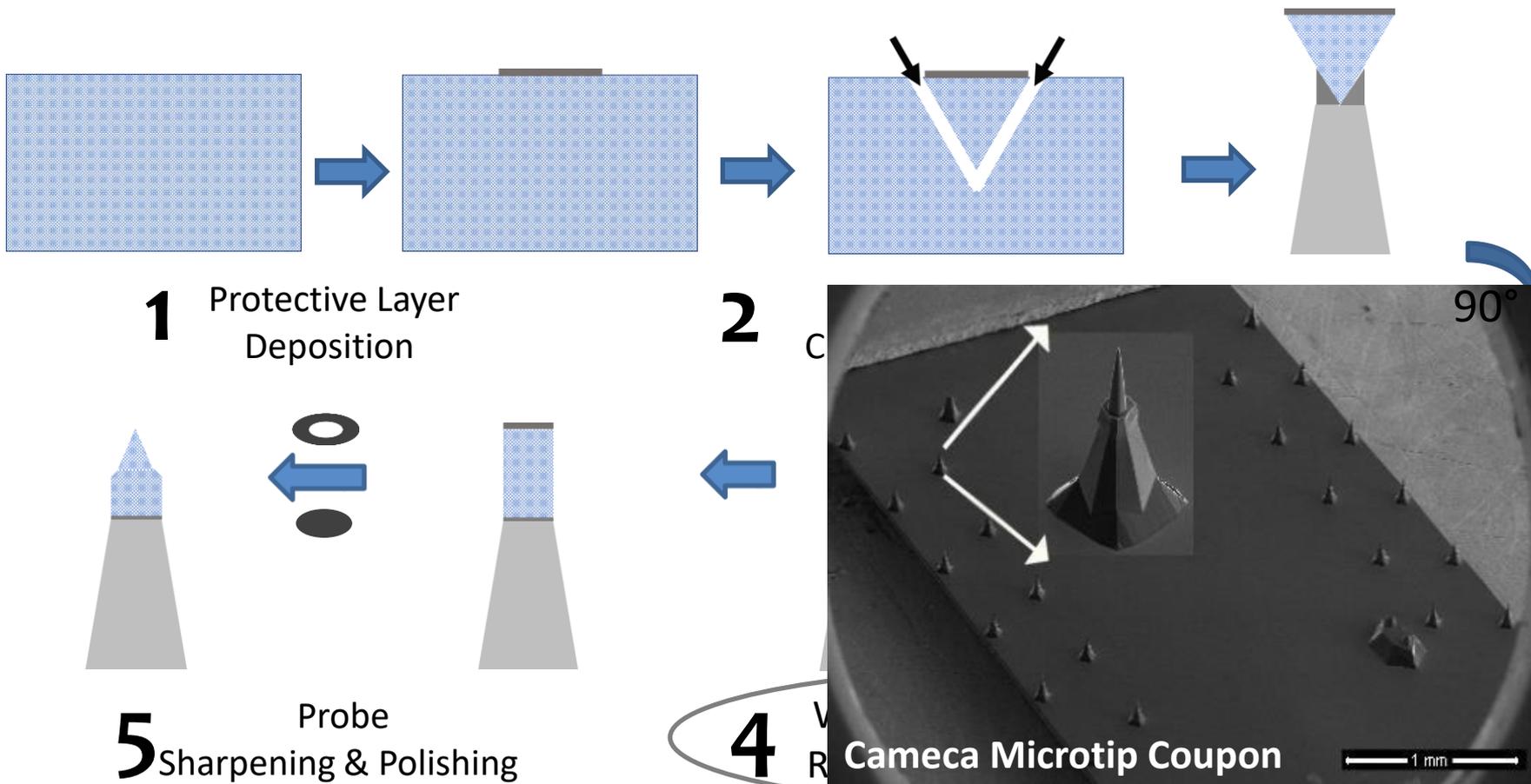


- Electrochemical process where material is removed leaving a sharp tip
- Polishing done using meniscus of electrolyte
- Electrolyte chosen based upon material being polished





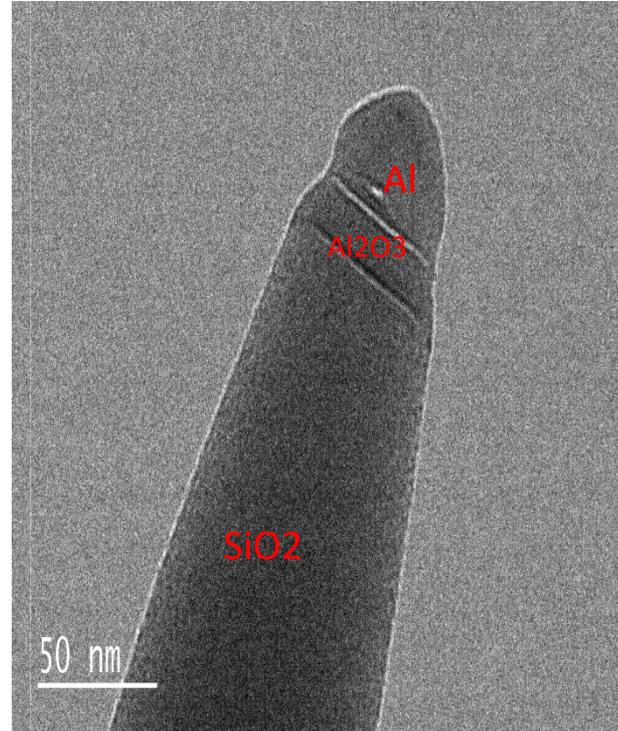
Schematic of APT-tip FIB Preparation



I Analysis of Dielectric Layer of Quantum Dot Devices

APT analysis of semiconductor quantum dot devices to investigate the effects of impurities and roughness at the interfaces around the Al_2O_3 dielectric layer.

Goal: To determine the relationship between transport properties of the quantum dot and interface imperfections.



Sputtered
Al (100 nm)

ALD Al_2O_3
(10-15 nm)

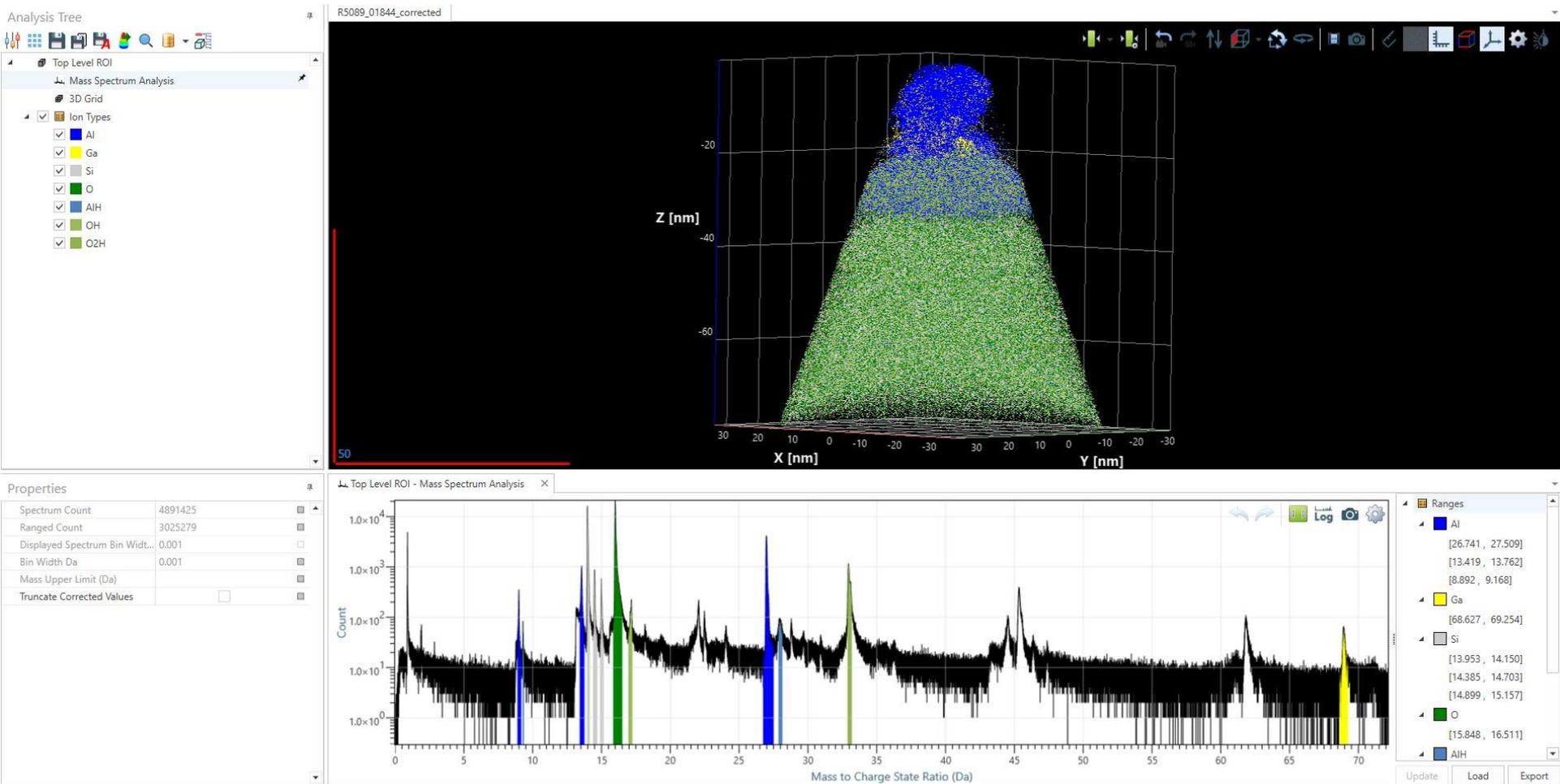
SiO_2 (1000 nm)

Si substrate

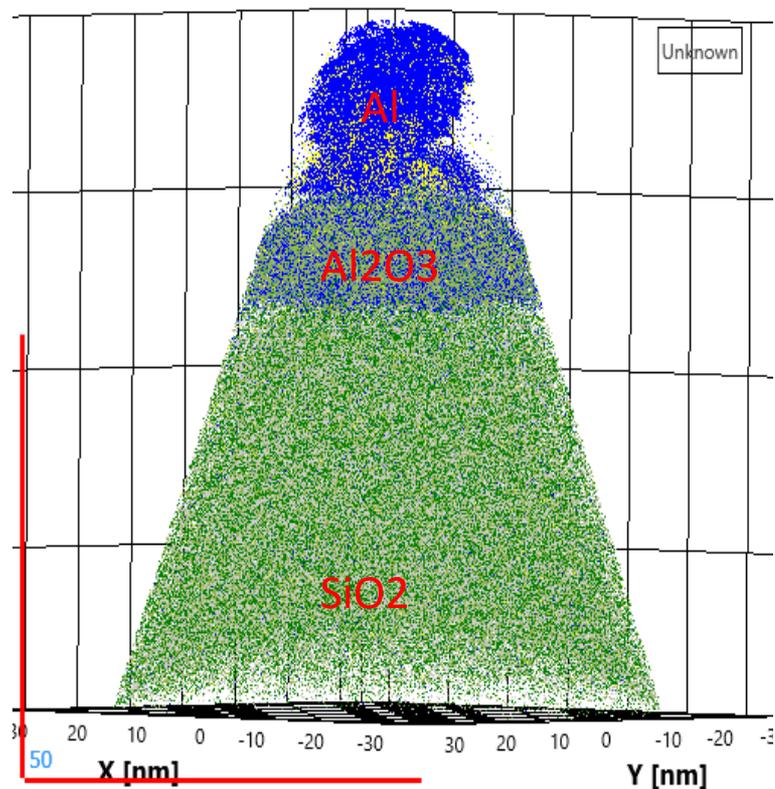
Courtesy: J. Huang and N. Mason, University of Illinois



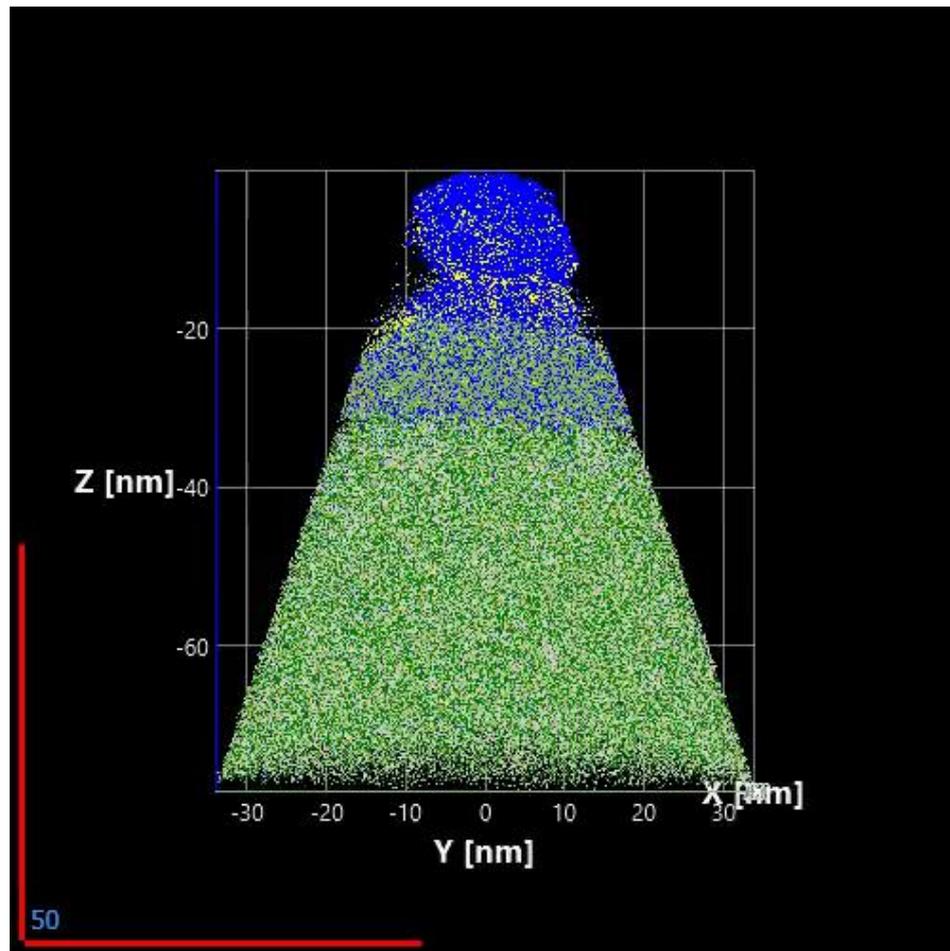
Analysis of Dielectric Layer of Quantum Dot Devices



APT Reconstruction: Al in blue, O in green, Si in gray, Ga in yellow.

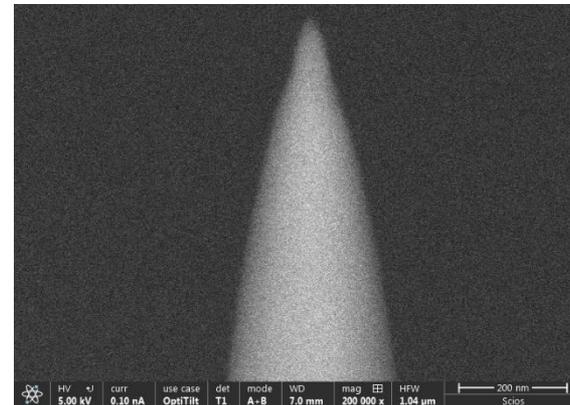
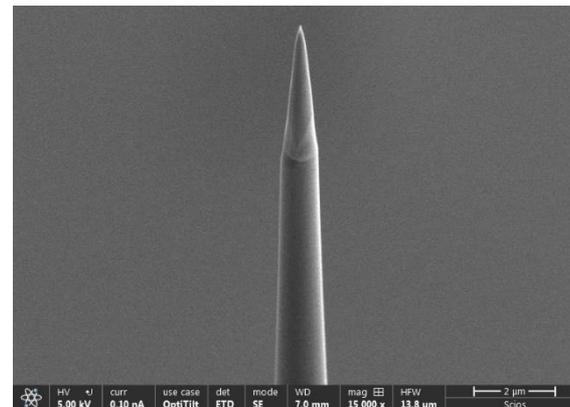


Al in blue, O in green, Si in gray



- FIB of needle specimen
- Approximately 80M hits in laser pulse mode
- Standard analysis using IVAS:
 - 1-D concentration profile
 - Cluster Analysis
 - Nearest Neighbor Analysis
 - Local Concentration
 - Cluster composition analysis for two separate regions
 - Cluster Size Analysis
 - Cluster Composition Analysis
 - Iso-surfaces
 - Si/Ni
 - Frequency Distribution Analysis

Samples courtesy: B. Heuser, University of Illinois
FIB preparation: H. Zhou, University of Illinois
APT measurement: W. Swiech, University of Illinois

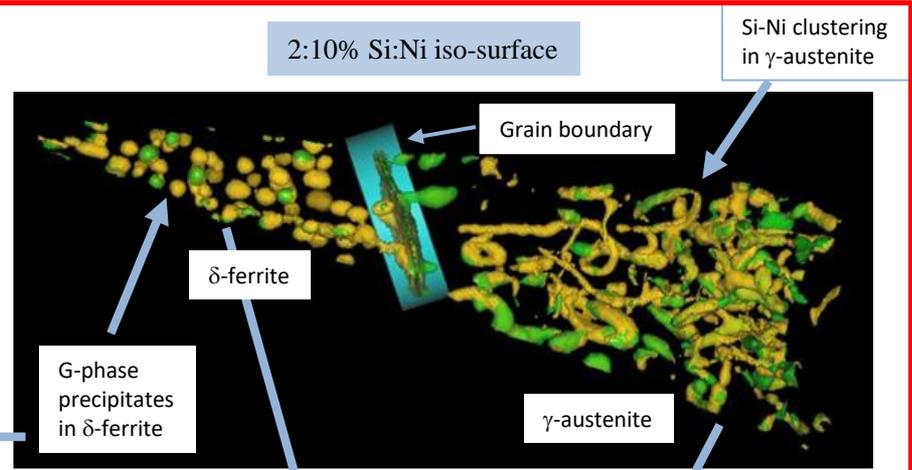
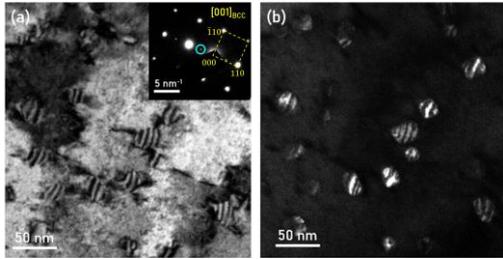


SEM Images

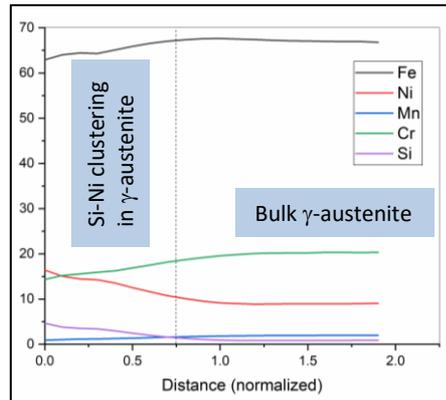
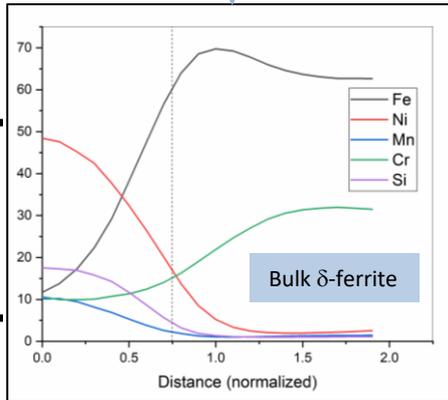
APT Analysis of Proton Irradiated Mixed Phase 308L Stainless Steel

Mixed phase: δ -ferrite and γ -austenite

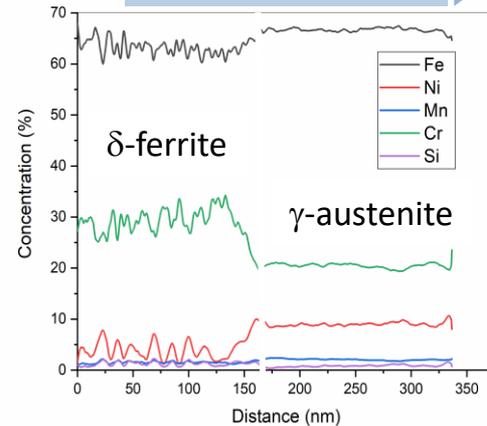
TEM dark field of G-phase particles



Cluster Analysis



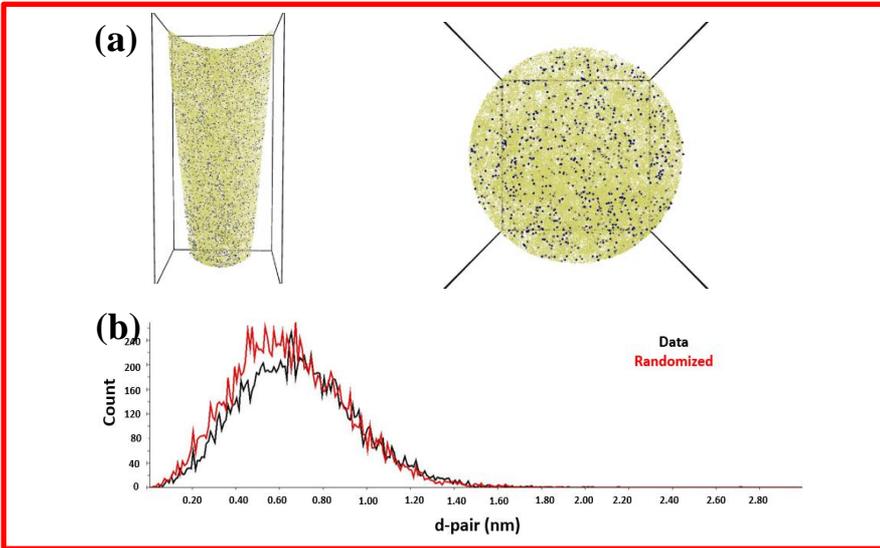
1-D composition profiles



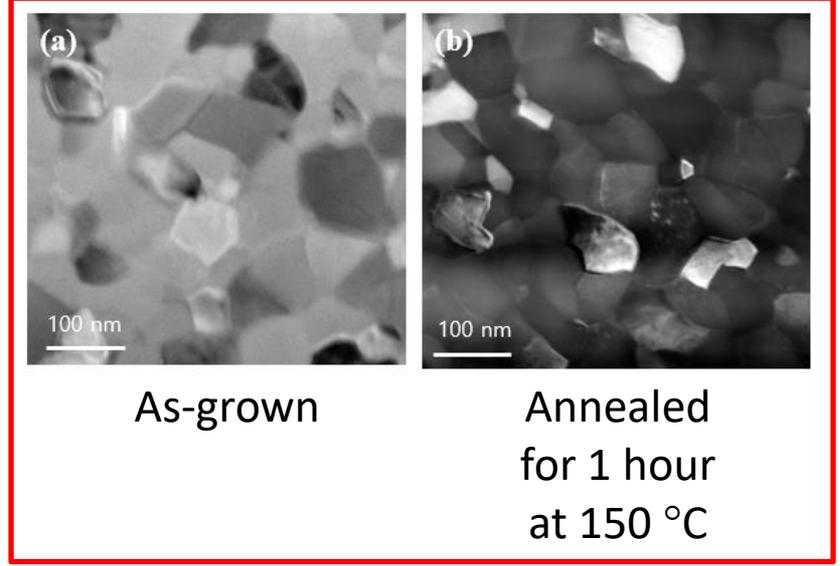
G-phase

APT analysis

Atom	Al	Sc	Ga	O	C	Pt	H
Composition (at.%)	98.17	1.37	0.1	0.01	0.01	0.04	0.32

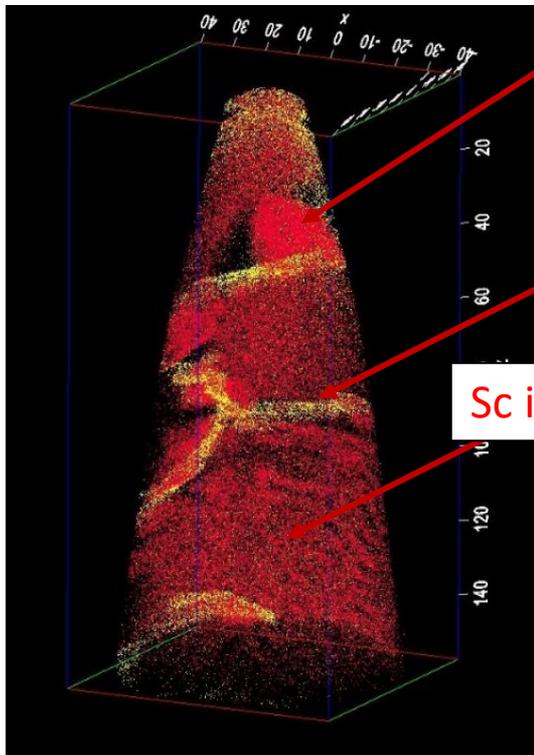


STEM analysis



Courtesy: S. Jana, S. Kim, R.S. Averback,
P. Bellon, University of Illinois

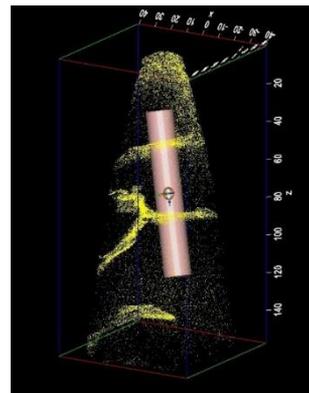
Grain Boundary Depletion: Annealing at 180 °C



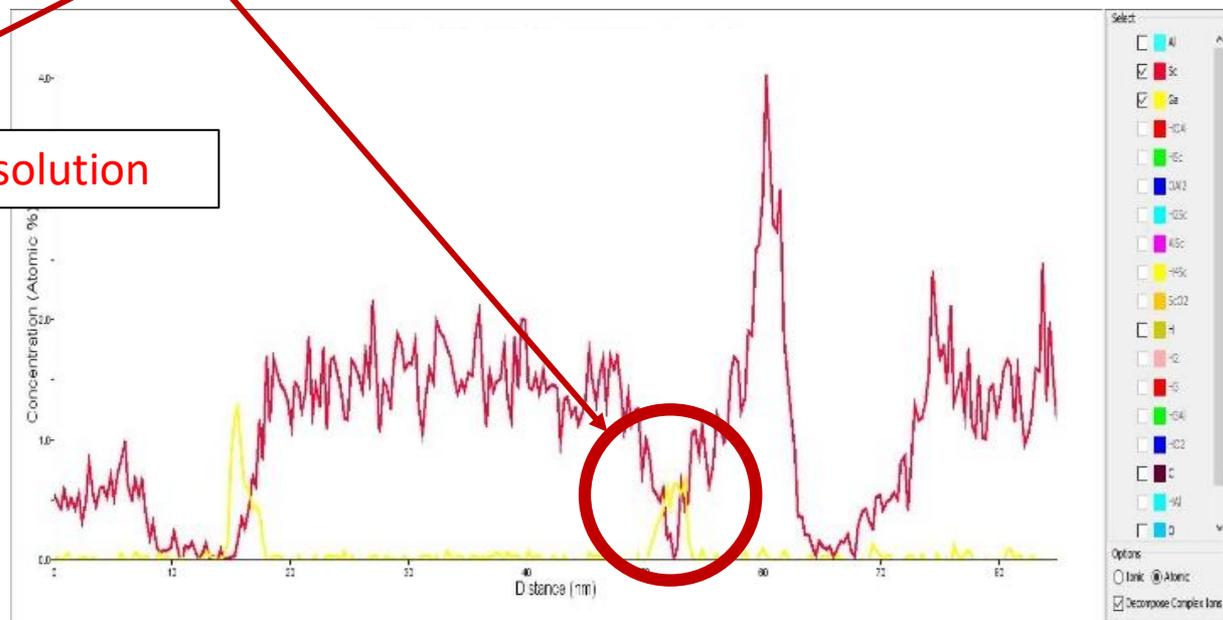
Sc-rich precipitate

Sc-depleted GB

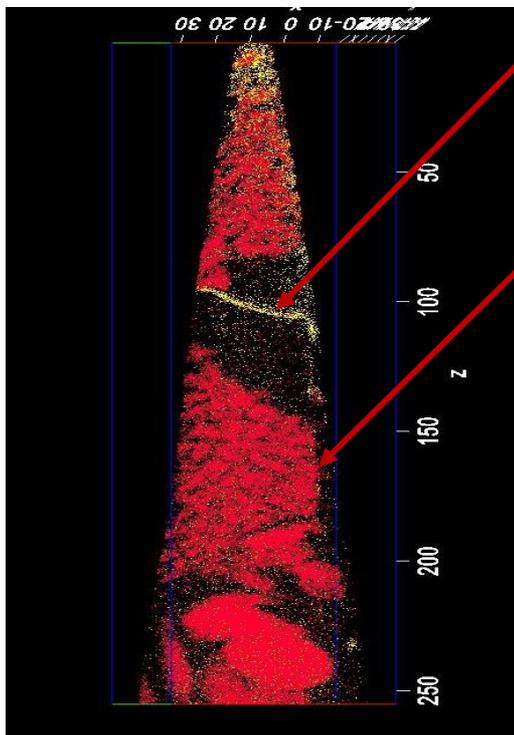
Sc in solution



1D concentration profile along cylinder

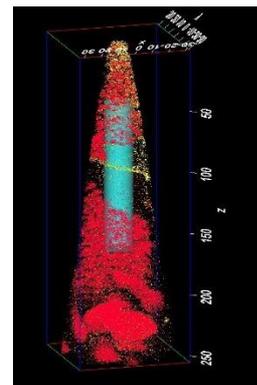


Grain Boundary Depletion: Annealing at 300 °C

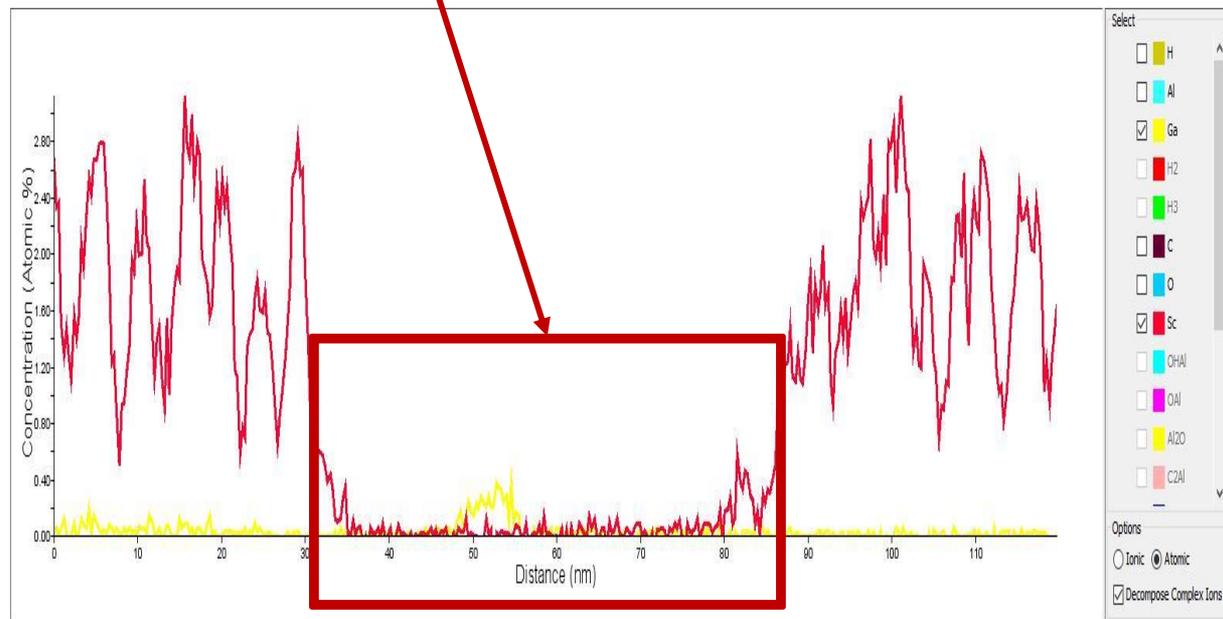


Sc-depleted GB

Sc-rich nanoclusters



1D concentration profile along cylinder



Spatial Resolution

0.1 – 0.3 nm in depth

0.3 – 0.5 nm laterally

Field of View

100 – 200 nm laterally

Time-of-flight mass analysis

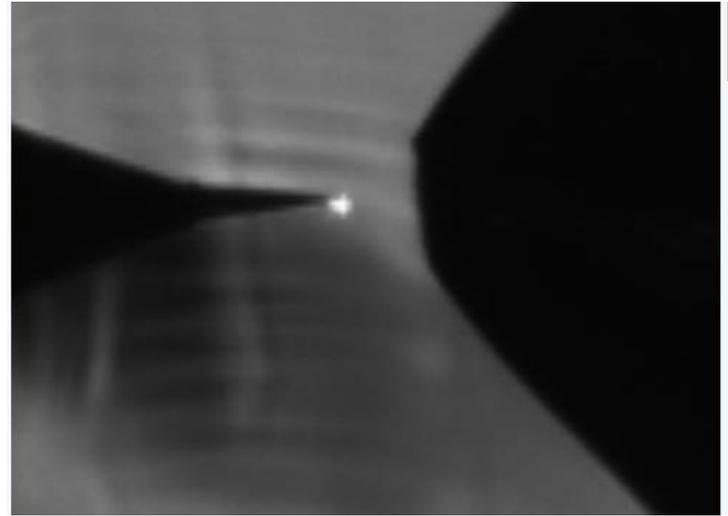
Mass range from 1 – 600 amu

Compositional analysis

Near 100% ionization of emitted atoms

Up to 80% of all atoms analyzed

Sensitivity ~ ppm



Well suited for analysis of

Precipitates

Grain boundaries

Isotopic variations

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